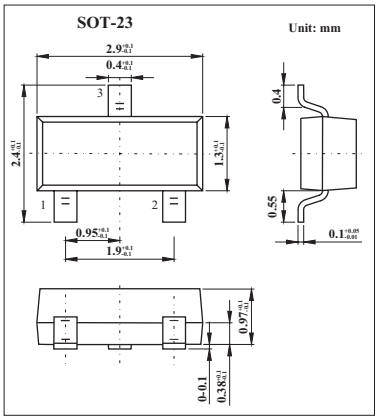
Silicon Schottky Barrier Diode

HSM88AS



Features

- Proof against high voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	10	V
Average rectified current	I_O	15	mA
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	I_F = 1 mA	350		420	mV
		I_F = 10 mA	500		580	
Reverse current	I_R	V_R = 2 V			0.2	μA
		V_R = 10 V			10	
Capacitance	C	V_R =0 V, f = 1 MHz			0.85	pF
Capacitance deviation	ΔC	V_R =0 V, f = 1 MHz			0.10	pF
Forward voltage deviation	ΔV_F	I_F = 10 mA			10	mV
ESD-Capability (Note 1)		C=200pF , Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; $I_R \geqslant$ 400nA at V_R =2 V

Marking

Marking	C1